

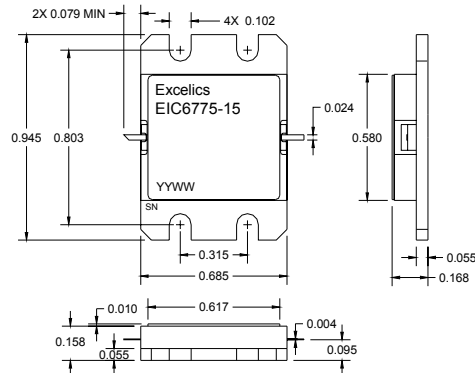
EIC6775-15

ISSUED 10/08/2008

6.70-7.50 GHz 15-Watt Internally Matched Power FET

FEATURES

- 6.70– 7.50GHz Bandwidth
- Input/Output Impedance Matched to 50 Ohms
- +42.0 dBm Output Power at 1dB Compression
- 7.5 dB Power Gain at 1dB Compression
- 31% Power Added Efficiency
- 100% Tested for DC, RF, and R_{TH}



Caution! ESD sensitive device.

ELECTRICAL CHARACTERISTICS ($T_a = 25^\circ\text{C}$)

SYMBOL	PARAMETERS/TEST CONDITIONS ¹	MIN	TYP	MAX	UNITS
P_{1dB}	Output Power at 1dB Compression $f = 6.70\text{-}7.50\text{GHz}$ $V_{DS} = 10\text{ V}, I_{DSQ} \approx 4500\text{mA}$	41.0	42.0		dBm
G_{1dB}	Gain at 1dB Compression $f = 6.70\text{-}7.50\text{GHz}$ $V_{DS} = 10\text{ V}, I_{DSQ} \approx 4500\text{mA}$	7.0	8.0		dB
ΔG	Gain Flatness $f = 6.70\text{-}7.50\text{GHz}$ $V_{DS} = 10\text{ V}, I_{DSQ} \approx 4500\text{mA}$			± 0.6	dB
PAE	Power Added Efficiency at 1dB Compression $V_{DS} = 10\text{ V}, I_{DSQ} \approx 4500\text{mA}$ $f = 6.70\text{-}7.50\text{GHz}$		31		%
I_{d1dB}	Drain Current at 1dB Compression $f = 6.70\text{-}7.50\text{GHz}$		4600	5200	mA
I_{DSS}	Saturated Drain Current $V_{DS} = 3\text{ V}, V_{GS} = 0\text{ V}$		8500	11000	mA
V_P	Pinch-off Voltage $V_{DS} = 3\text{ V}, I_{DS} = 85\text{ mA}$		-2.5	-4.0	V
R_{TH}	Thermal Resistance ²		2.0	2.5	$^\circ\text{C}/\text{W}$

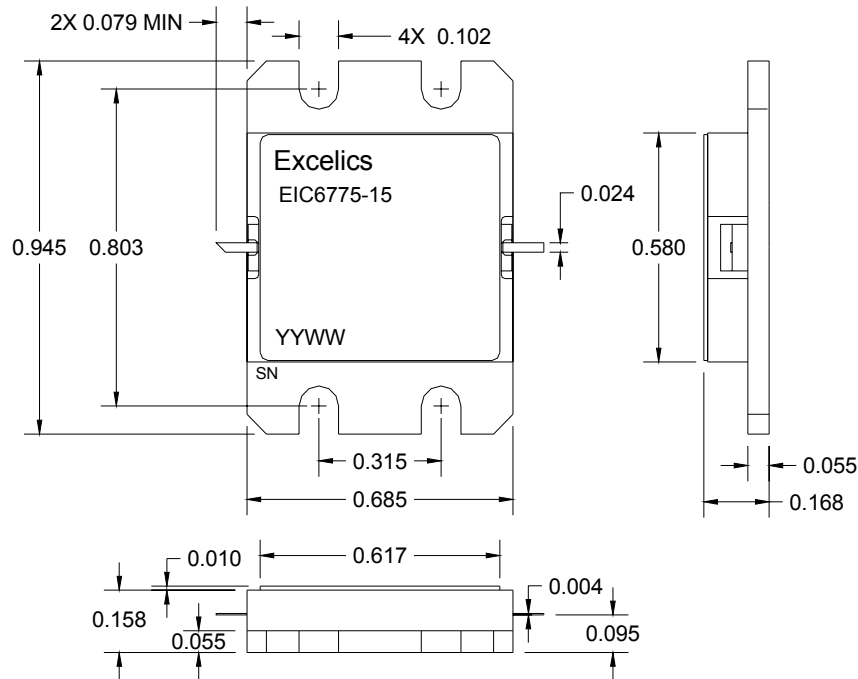
Note: 1. Tested with 50 Ohm gate resistor.
2. Overall R_{th} depends on case mounting.

ABSOLUTE MAXIMUM RATING^{1,2}

SYMBOLS	PARAMETERS	ABSOLUTE ¹	CONTINUOUS ²
V_{ds}	Drain-Source Voltage	15	10V
V_{gs}	Gate-Source Voltage	-5	-3V
I_{gsf}	Forward Gate Current	189.9mA	63.3mA
I_{gsr}	Reverse Gate Current	-10.6mA	-31.7mA
P_{in}	Input Power	41.5dBm	@ 3dB Compression
T_{ch}	Channel Temperature	175 $^\circ\text{C}$	175 $^\circ\text{C}$
T_{stg}	Storage Temperature	-65 to +175 $^\circ\text{C}$	-65 to +175 $^\circ\text{C}$
P_t	Total Power Dissipation	60W	60W

Note: 1. Exceeding any of the above ratings may result in permanent damage.
2. Exceeding any of the above ratings may reduce MTTF below design goals.

PACKAGES OUTLINE (Hermetic)



Note: Dimensions in inches, Tolerance \pm .005 unless otherwise specified

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